Hall Ticke	t No									Question Paper Code: AHS006			
INSTITUTE OF AERONAUTICAL ENGINEERING													

B.Tech I Semester End Examinations (Regular) - December, 2016 **Regulation: IARE – R16 ENGINEERING PHYSICS** (Common for CSE/IT/ECE/EEE)

Time: 3 Hours

Max Marks: 70

Answer ONE Question from each Unit All Questions Carry Equal Marks All parts of the question must be answered in one place only

$\mathbf{UNIT} - \mathbf{I}$

- 1. (a) What is internal field in a dielectric? Obtain an expression for internal field for a one dimensional array of dipoles and extend it to a cubic solid. [7M]
 - (b) Explain the mechanisms of ionic and orientation polarization. Which one of them does not depend on temperature? [7M]
- 2. (a) Distinguish between para and diamagnetism. Give one example for each class of material. [7M]
 - (b) Define magnetic field intensity (H) and magnetic induction (B). Derive relation between B&H.

[7M]

$\mathbf{UNIT} - \mathbf{II}$

3.	(a) Explain the construction of working ruby laser with energy level diagram	[7M]
	(b) What is ratio of populations of the two energy levels correspondence to the lasing w 694.3nm in ruby laser	avelength of $[7M]$
4.	(a) Define the term laser. What are the characteristics of laser beam ?	[7M]

(b) Describe the construction of He-Ne laser and explain its working with the help of energy level diagram. [7M]

$\mathbf{UNIT} - \mathbf{III}$

- 5. (a) Compare the surface to volume ratios of a spherical object when the size (radius) is reduced from 1000 cm to 1 nm. [7M]
 - (b) What are the causes for drastic changes in properties of a material when its size is reduced to the nanoscale? Explain. List some important applications of nano materials. [7M]
- 6. (a) Outline the sol gel and chemical vapour deposition techniques for the preparation of nano materials with emphasis on the merits of each process [7M]
 - (b) What are the main parts of a transmission electron microscope? Explain the working of a TEM and list the applications of TEM. [7M]

$\mathbf{UNIT}-\mathbf{IV}$

- (a) Obtain the wave function for a particle in an infinite potential well along with normalization condition. Specify wave function, energy and the probability densities for the ground and first two excited
 - (b) An electron is in the ground state in an infinite potential well of width $5A^0$, calculate the excitation energy required to raise the electron to the third excited state. [7M]
- 8. (a) Setup the time independent one dimensional Schrödinger wave equation. [7M]
 - (b) Explain the deBroglie hypothesis and derive expression for deBroglie wavelength. Calculate the deBroglie wavelengths of a photon and a proton having energy of 100 eV (Mass of proton $=1.67 \times 10^{-27} kg$). [7M]

$\mathbf{UNIT} - \mathbf{V}$

- 9. (a) Calculate the Hall coefficients in semiconductors with carrier densities equal to i. $1.9 \times 10^{14}/cm^3$
 - ii. 1.6 $\times 10^{17}/cm^3$
 - (b) Determine the Fermi energy in the following cases with suitable energy level diagrams [7M]i. Intrinsic semiconductor
 - ii. P-type semiconductor
 - iii. n-type semiconductor
- 10. (a) What is the hall effect? Obtain the expression for hall coefficient. [7M]
 - (b) Mobilities of electrons and holes in a sample of intrinsic germanium at 300K are $0.36m^2V^{-1}s^{-1}$ and $0.17m^2V^{-1}s^{-1}$ respectively. If the resistivity of the specimen is $2.12\Omega - m$, compute the forbidden energy gap for germanium. [7M]